

IGBT - Field Stop 600 V, 20 A

FGH20N60UFD

Description

Using novel field stop IGBT Technology, ON Semiconductor's field stop IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.

Features

- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.8 \text{ V @ } I_C = 20 \text{ A}$
- High Input Impedance
- Fast Switching
- This Device is Pb-Free and is RoHS Compliant

Applications

- Solar Inverter, UPS, Welder, PFC

ABSOLUTE MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|----------------------|--------------|------------------|
| Collector to Emitter Voltage | V_{CES} | 600 | V |
| Gate to Emitter Voltage | V_{GES} | ± 20 | V |
| Transient Gate to Emitter Voltage | | ± 30 | |
| Collector Current @ $T_c = 25^\circ\text{C}$ @ $T_c = 100^\circ\text{C}$ | I_C | 40 | A |
| | | 20 | |
| Pulsed Collector Current @ $T_c = 25^\circ\text{C}$ | I_{CM} (Note 1) | 60 | A |
| Diode Forward Current @ $T_c = 25^\circ\text{C}$ @ $T_c = 100^\circ\text{C}$ | I_F | 20 | A |
| | | 10 | |
| Pulsed Diode Maximum Forward Current | I_{FM} (Note 1) | 60 | A |
| Maximum Power Dissipation @ $T_c = 25^\circ\text{C}$ @ $T_c = 100^\circ\text{C}$ | P_D | 165 | W |
| | | 66 | |
| Operating Junction Temperature | T_J | -55 to + 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | -55 to + 150 | $^\circ\text{C}$ |
| Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | T_L | 300 | $^\circ\text{C}$ |

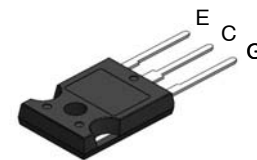
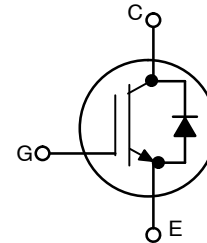
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: Pulse width limited by max. junction temperature.



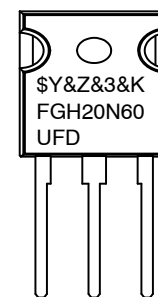
ON Semiconductor®

www.onsemi.com



TO-247-3LD
CASE 340CK

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
 &Z = Assembly Plant Code
 &3 = Numeric Date Code
 &K = Lot Code
 FGH20N60UFD = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FGH20N60UFD

THERMAL CHARACTERISTICS

| Parameter | Symbol | Typ. | Max. | Unit |
|--|-----------------|------|------|------|
| Thermal Resistance Junction-to-Case, for IGBT | $R_{\theta JC}$ | – | 0.76 | °C/W |
| Thermal Resistance Junction-to-Case, for Diode | $R_{\theta JC}$ | – | 2.51 | °C/W |
| Thermal Resistance Junction-to-Ambient | $R_{\theta JA}$ | – | 40 | °C/W |

PACKAGE MARKING AND ORDERING INFORMATION

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|---------------|-------------|---------|----------------|-----------|------------|----------|
| FGH20N60UFDTU | FGH20N60UFD | TO-247 | Tube | N/A | N/A | 30 Units |

ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|-----------|--------|-----------------|-----|-----|-----|------|
|-----------|--------|-----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|--|------------------------------|---|-----|-----|------|---------------|
| Collector to Emitter Breakdown Voltage | BV_{CES} | $V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$ | 600 | – | – | V |
| Temperature Coefficient of Breakdown Voltage | $\Delta BV_{CES}/\Delta T_J$ | $V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$ | – | 0.6 | – | V/°C |
| Collector Cut-Off Current | I_{CES} | $V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$ | – | – | 250 | μA |
| G-E Leakage Current | I_{GES} | $V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$ | – | – | ±400 | nA |

ON CHARACTERISTICS

| | | | | | | |
|---|---------------|--|-----|-----|-----|---|
| G-E Threshold Voltage | $V_{GE(th)}$ | $I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$ | 4.0 | 5.0 | 6.5 | V |
| Collector to Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 20\text{ A}, V_{GE} = 15\text{ V}$ | – | 1.8 | 2.4 | V |
| | | $I_C = 20\text{ A}, V_{GE} = 15\text{ V}, T_C = 125^\circ\text{C}$ | – | 2.0 | – | V |

DYNAMIC CHARACTERISTICS

| | | | | | | |
|------------------------------|-----------|---|---|-----|---|----|
| Input Capacitance | C_{ies} | $V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | – | 940 | – | pF |
| Output Capacitance | C_{oes} | | – | 110 | – | pF |
| Reverse Transfer Capacitance | C_{res} | | – | 40 | – | pF |

SWITCHING CHARACTERISTICS

| | | | | | | |
|--------------------------|--------------|--|---|------|----|----|
| Turn-On Delay Time | $t_{d(on)}$ | $V_{CC} = 400\text{ V}, I_C = 20\text{ A}, R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$ | – | 13 | – | ns |
| Rise Time | t_r | | – | 17 | – | ns |
| Turn-Off Delay Time | $t_{d(off)}$ | | – | 87 | – | ns |
| Fall Time | t_f | | – | 32 | 64 | ns |
| Turn-On Switching Loss | E_{on} | | – | 0.38 | – | mJ |
| Turn-Off Switching Loss | E_{off} | | – | 0.26 | – | mJ |
| Total Switching Loss | E_{ts} | | – | 0.64 | – | mJ |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{CC} = 400\text{ V}, I_C = 20\text{ A}, R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 125^\circ\text{C}$ | – | 13 | – | ns |
| Rise Time | t_r | | – | 16 | – | ns |
| Turn-Off Delay Time | $t_{d(off)}$ | | – | 92 | – | ns |
| Fall Time | t_f | | – | 63 | – | ns |
| Turn-On Switching Loss | E_{on} | | – | 0.41 | – | mJ |
| Turn-Off Switching Loss | E_{off} | | – | 0.36 | – | mJ |
| Total Switching Loss | E_{ts} | | – | 0.77 | – | mJ |
| Total Gate Charge | Q_g | $V_{CE} = 400\text{ V}, I_C = 20\text{ A}, V_{GE} = 15\text{ V}$ | – | 63 | – | nC |
| Gate to Emitter Charge | Q_{ge} | | – | 7 | – | nC |
| Gate to Collector Charge | Q_{gc} | | – | 32 | – | nC |

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ELECTRICAL CHARACTERISTICS OF THE DIODE ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parametr | Symbol | Test Conditions | Min | Typ | Max | Unit | |
|-------------------------------|----------|---|---------------------------|-----|-----|------|----|
| Diode Forward Voltage | V_{FM} | $I_F = 10\text{ A}$ | $T_C = 25^\circ\text{C}$ | - | 1.9 | 2.5 | V |
| | | | $T_C = 125^\circ\text{C}$ | - | 1.7 | - | |
| Diode Reverse Recovery Time | t_{rr} | $I_F = 10\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}$ | $T_C = 25^\circ\text{C}$ | - | 34 | - | ns |
| | | | $T_C = 125^\circ\text{C}$ | - | 57 | - | |
| Diode Reverse Recovery Charge | Q_{rr} | | $T_C = 25^\circ\text{C}$ | - | 41 | - | nC |
| | | | $T_C = 125^\circ\text{C}$ | - | 96 | - | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

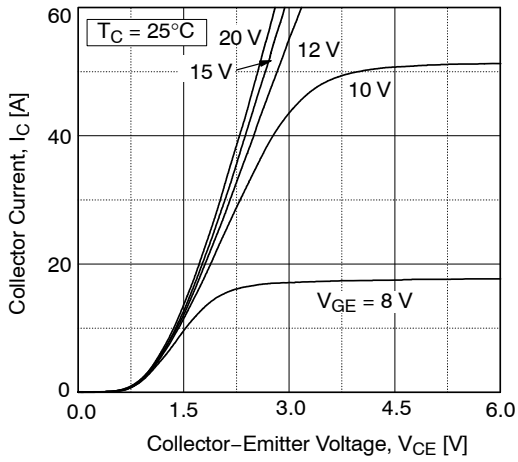


Figure 1. Typical Output Characteristics

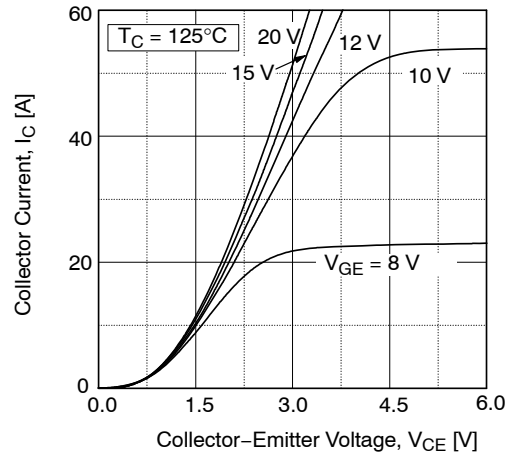


Figure 2. Typical Output Characteristics

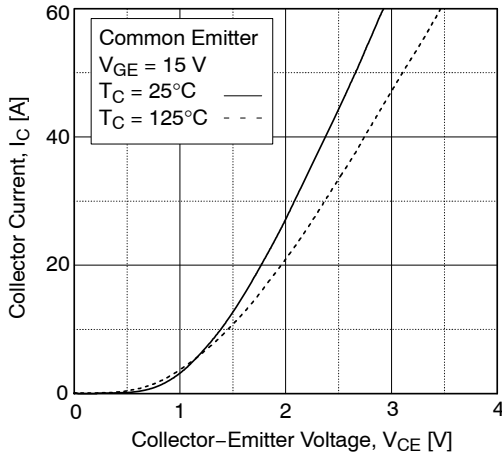


Figure 3. Typical Saturation Voltage Characteristics

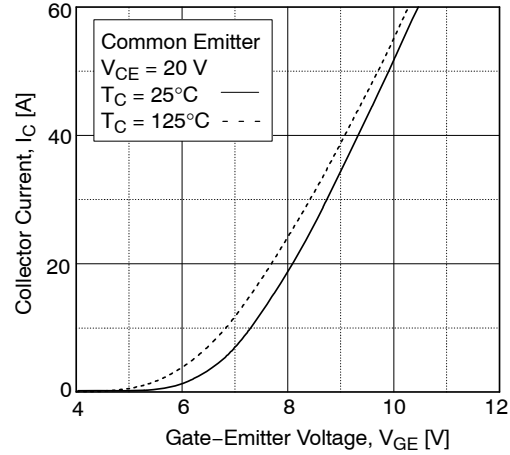


Figure 4. Transfer Characteristics

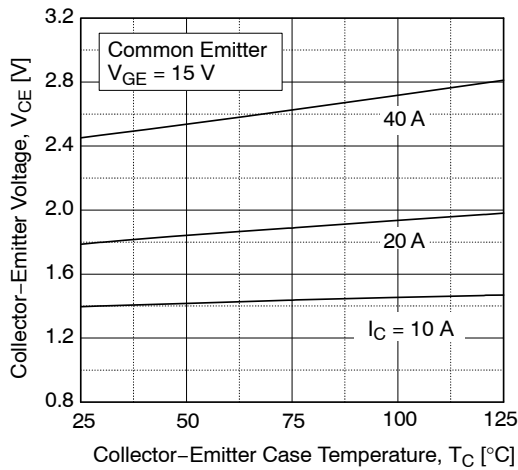


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

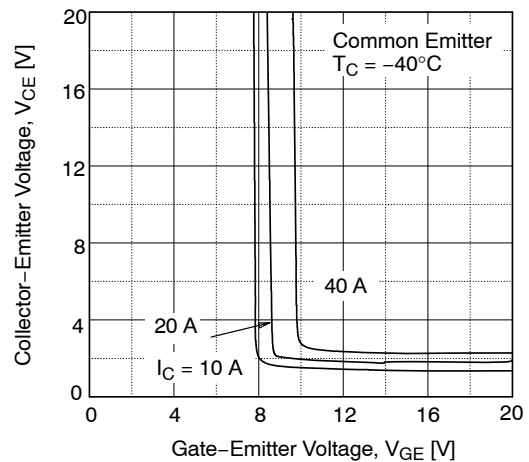


Figure 6. Saturation Voltage vs. Vge

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TYPICAL CHARACTERISTICS

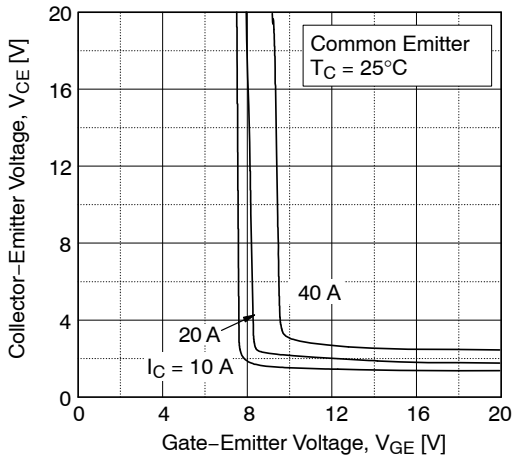


Figure 7. Saturation Voltage vs. V_{GE}

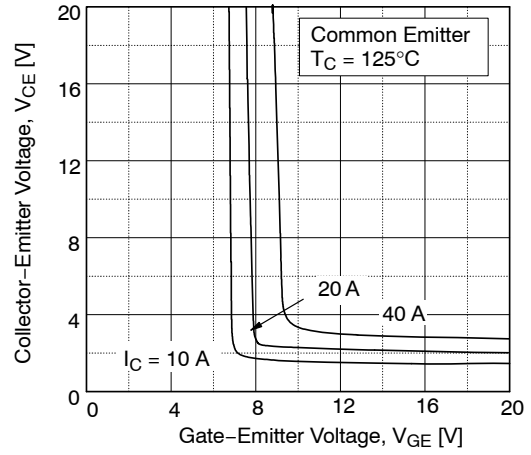


Figure 8. Saturation Voltage vs. V_{GE}

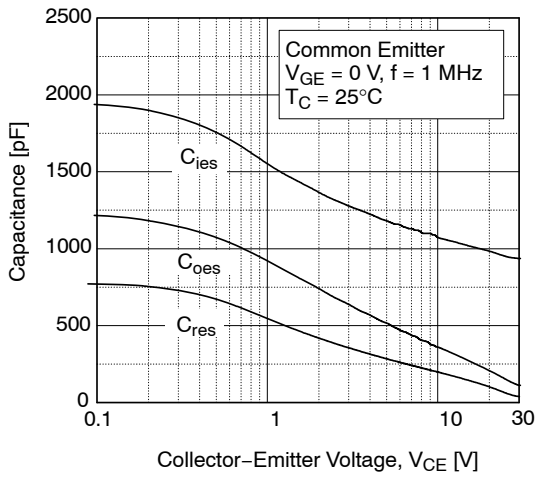


Figure 9. Capacitance Characteristics

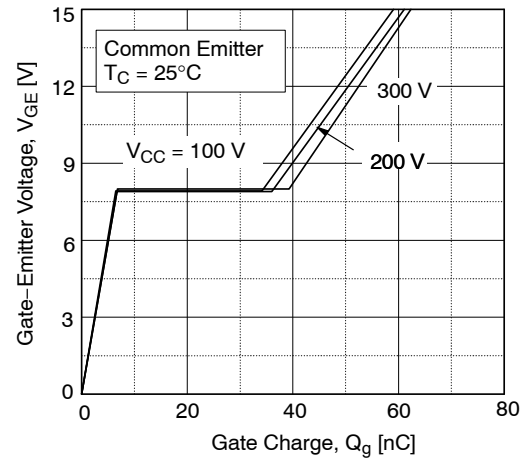


Figure 10. Gate Charge Characteristics

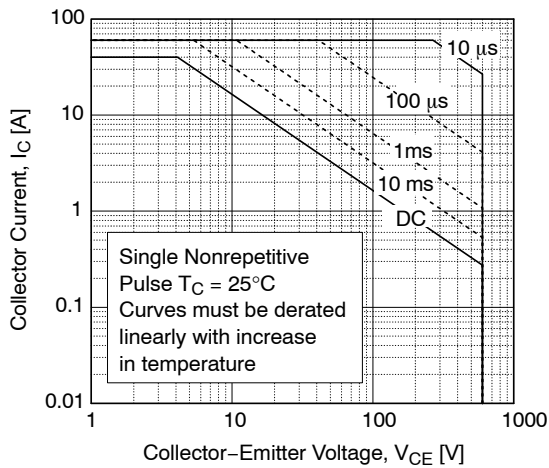


Figure 11. SOA Characteristics

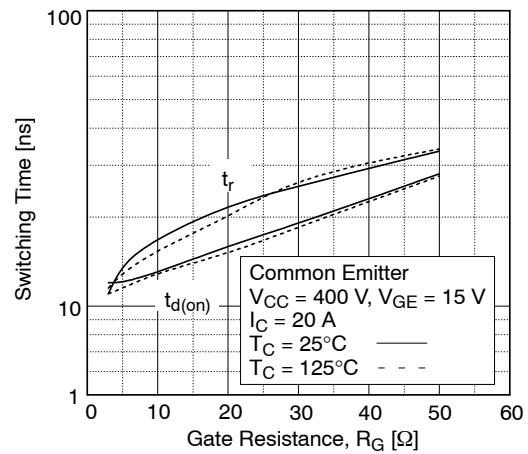


Figure 12. Turn-on Characteristics vs. Gate Resistance

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TYPICAL CHARACTERISTICS

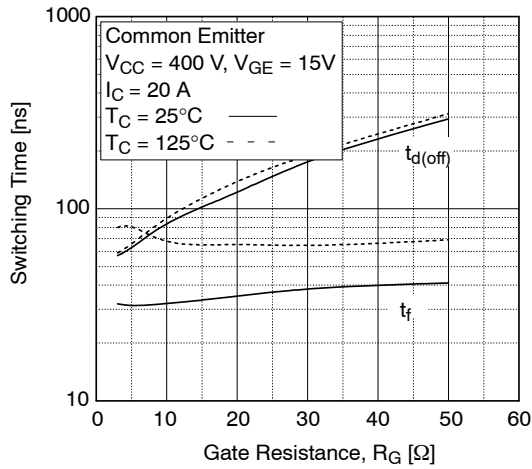


Figure 13. Turn-off Characteristics vs. Gate Resistance

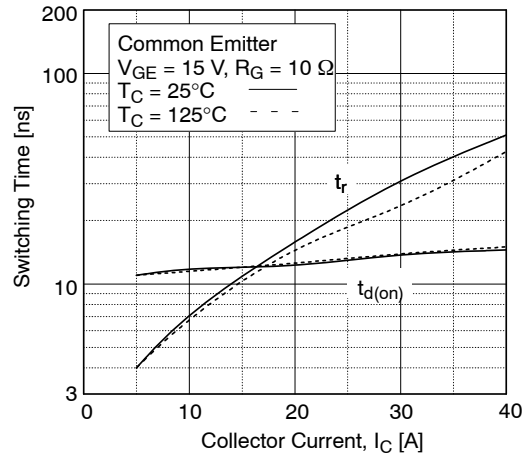


Figure 14. Turn-on Characteristics vs. Collector Current

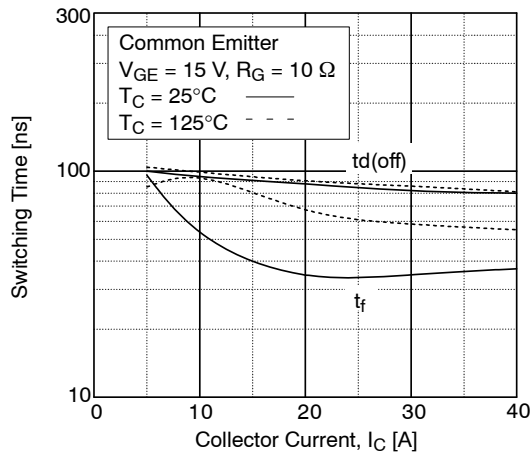


Figure 15. Turn-off Characteristics vs. Collector Current

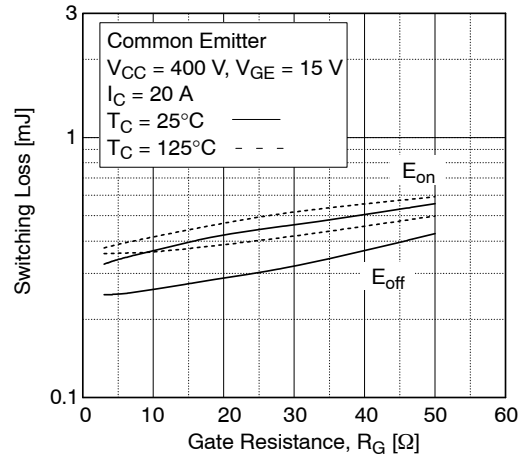


Figure 16. Switching Loss vs. Gate Resistance

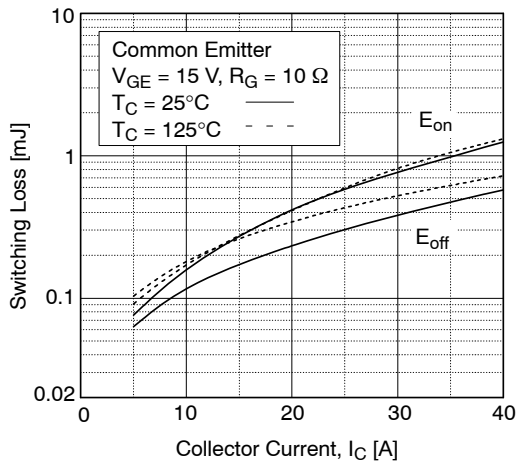


Figure 17. Switching Loss vs. Collector Current

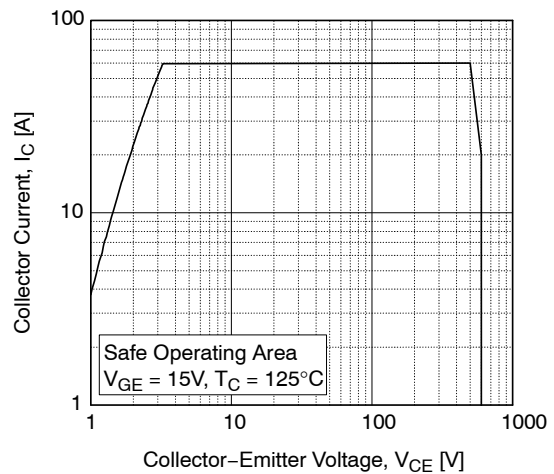


Figure 18. Turn-off Switching SOA Characteristics

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TYPICAL CHARACTERISTICS

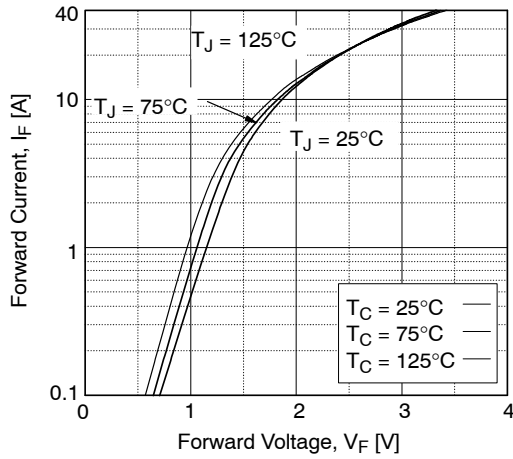


Figure 19. Forward Characteristics

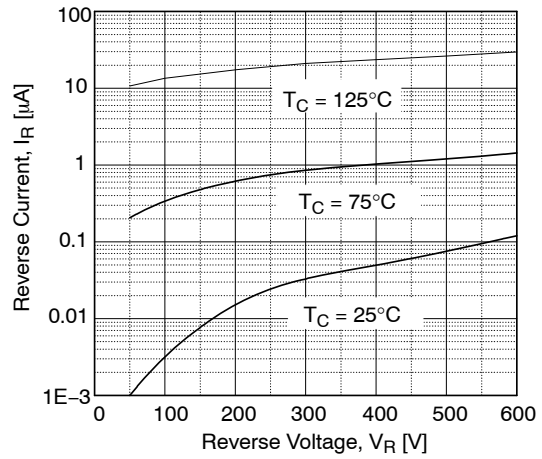


Figure 20. Reverse Current

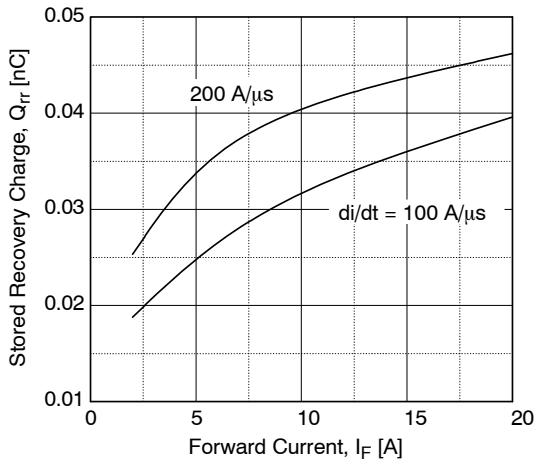


Figure 21. Stored Charge

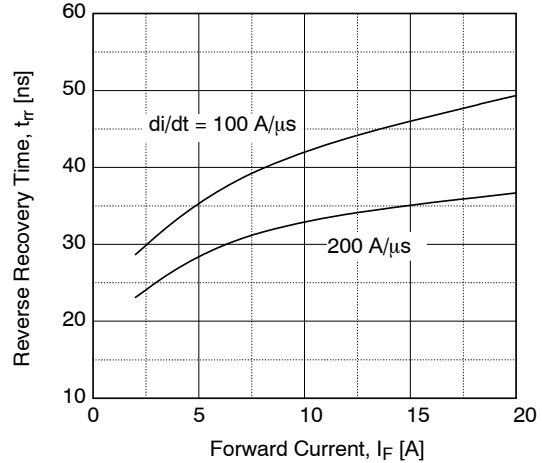


Figure 22. Reverse Recovery Time

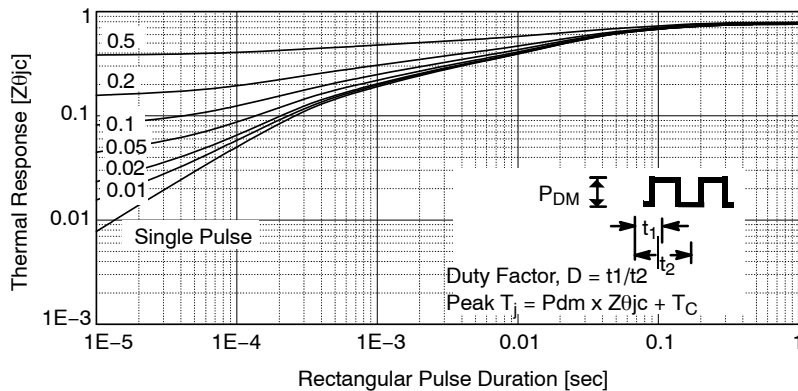


Figure 23. Transient Thermal Impedance of IGBT



TO-247-3LD SHORT LEAD
CASE 340CK
ISSUE A

DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| DIM | MILLIMETERS | | |
|-----|-------------|-------|-------|
| | MIN | NOM | MAX |
| A | 4.58 | 4.70 | 4.82 |
| A1 | 2.20 | 2.40 | 2.60 |
| A2 | 1.40 | 1.50 | 1.60 |
| b | 1.17 | 1.26 | 1.35 |
| b2 | 1.53 | 1.65 | 1.77 |
| b4 | 2.42 | 2.54 | 2.66 |
| c | 0.51 | 0.61 | 0.71 |
| D | 20.32 | 20.57 | 20.82 |
| D1 | 13.08 | ~ | ~ |
| D2 | 0.51 | 0.93 | 1.35 |
| E | 15.37 | 15.62 | 15.87 |
| E1 | 12.81 | ~ | ~ |
| E2 | 4.96 | 5.08 | 5.20 |
| e | ~ | 5.56 | ~ |
| L | 15.75 | 16.00 | 16.25 |
| L1 | 3.69 | 3.81 | 3.93 |
| ØP | 3.51 | 3.58 | 3.65 |
| ØP1 | 6.60 | 6.80 | 7.00 |
| Q | 5.34 | 5.46 | 5.58 |
| S | 5.34 | 5.46 | 5.58 |

| | | |
|-------------------------|-----------------------|--|
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| DESCRIPTION: | TO-247-3LD SHORT LEAD | PAGE 1 OF 1 |

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